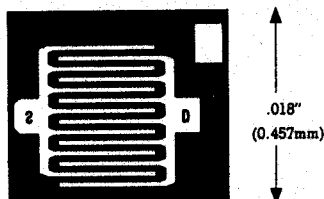


CHIP NUMBER  
**FN7.1**



.023"  
(0.584mm)

Die Size: 18 x 23 (mils)  
0.457 x .0584(mm)  
3 x 3 (mils)  
Pad Size: 0.076 x 0.076(mm)  
GATE-SUBSTRATE

#### CONTACT METALLIZATION

Top Contact: > 12,000  
Å Aluminum

Backside Contact: 3,000 Å Gold

#### ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

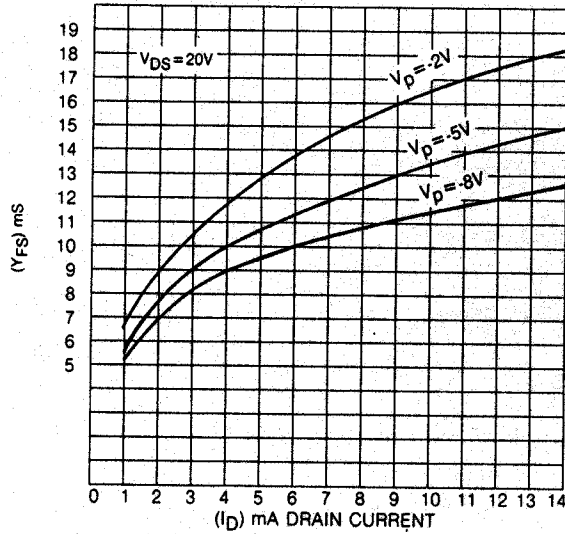
### TYPICAL ELECTRICAL CHARACTERISTICS

| PARAMETER     | MIN. | TYP  | MAX. | UNIT            | TEST CONDITIONS                     |
|---------------|------|------|------|-----------------|-------------------------------------|
| $B_{VGSS}$    | -30  | -50  | -70  | V               | $V_{DS} = 0, I_G = 1\mu A$          |
| $I_{DSS}$     | 5.0  | 60   | 150  | mA              | $V_{DS} = 20V, V_{GS} = 0$          |
| $g_{fs}$      |      | 8    |      | mmho            | $V_{DS} = 20V, I_D = 2mA$           |
| $I_{GSS}$     |      | -20  | -200 | pA              | $V_{GS} = -20V, V_{DS} = 0$         |
| $r_{DS}$      | 20   | 40   | 100  | $\Omega$        | $V_{DS} = 100mV, V_{GS} = 0$        |
| $V_{GS(off)}$ | -0.5 | -4.5 | -10  | V               | $V_{DS} = 20V, I_D = 1nA$           |
| $C_{rss}$     | 3.0  | 3.5  | 4.0  | pF              | $V_{DS} = 15V, I_D = 5mA, f = 1MHz$ |
| $C_{iss}$     | 10   | 12   | 16   | pF              | $V_{DS} = 15V, I_D = 5mA, f = 1MHz$ |
| $\bar{e}_n$   |      | 7    |      | nV/ $\sqrt{Hz}$ | $V_{DS} = 15V, I_D = 5mA, f = 1KHz$ |

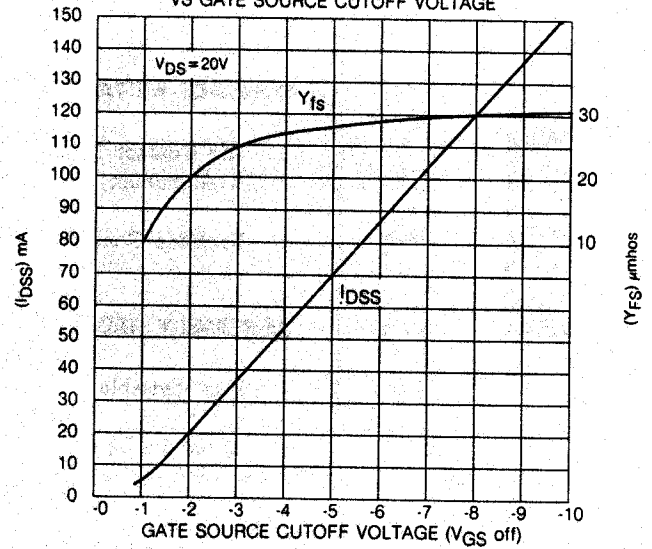
TYPICAL DEVICE TYPES: 2N4091 - 2N4093, 2N4391 - 2N4393, 2N4856 - 2N4861, KK4391 - KK4393

CHIP TYPE FN7.1

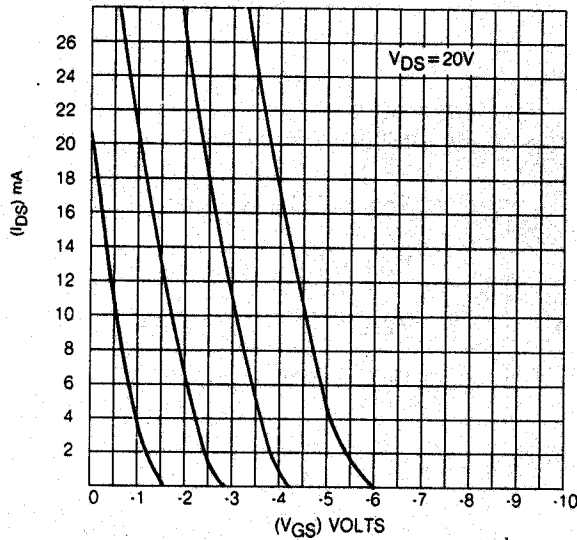
FORWARD TRANSADMITTANCE



SHORT CIRCUIT FORWARD TRANSADMITTANCE  
VS GATE SOURCE CUTOFF VOLTAGE



TRANSFER CHARACTERISTICS



COMMON SOURCE DRAIN CHARACTERISTICS

